



04-19-0

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## IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of

Group Art Unit:

CHEN, Ling and CAO, Wei

Examiner: Not Yet Assigned

Application No.: 10/050,654

Filing Date: January 16, 2002

For: **METHOD FOR GROWING THIN FILMS BY CATALYTIC ENHANCEMENT**

Box IDS  
Asst. Commissioner for Patents  
Washington, D.C. 20231

Dear Sir:

Applicant submits herewith patents, publications or other information (attached hereto and listed on the attached Form PTO-1449) of which he is aware, pursuant to his duty to disclose in accordance with 37 C.F.R. § 1.56.

This Information Disclosure Statement is filed before the mailing of the first Office Action on the merits as set forth in 37 C.F.R. § 1.97.

A list of the patent(s) or publication(s) is set forth on the attached Form PTO-1449 (Modified). A copy of each of the items listed on form PTO-1449 is supplied herewith.

A concise explanation of relevance of the items listed on PTO-1449 is not given. The Examiner is reminded that a "concise explanation of the relevance" of the submitted prior art "may be nothing more than identification of the particular figure or paragraph of the patent or publication which has some relation to the claimed invention," MPEP § 609.

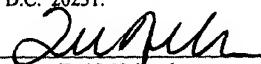
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## INFORMATION DISCLOSURE STATEMENT

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I hereby certify that the correspondence enclosed herein is being deposited as first class mail with the United States Postal Service on this date April 17, 2002, in an envelope addressed to: Asst. Commissioner for Patents, Washington, D.C. 20231.

By: 

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an admission that any patent, publication or other information referred to therein is "prior art" for this invention unless specifically designated as such.

In accordance with 37 C.F.R. § 1.97(g), the filing of this Information Disclosure Statement shall not be construed to mean that a search has been made or that no other material information as defined in 37 C.F.R. § 1.56(a) exists. Furthermore, pursuant to 37 C.F.R. § 1.97(h), the filing of this Information Disclosure Statement shall not be construed to be an admission that the information cited in this statement is, or is considered to be, material to patentability, as defined in 1.56(b). It is submitted that the Information Disclosure Statement is in compliance with 37 C.F.R. § 1.98 and MPEP § 609 and the Examiner is respectfully requested to consider the listed references.

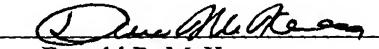
The Commissioner is hereby authorized to charge any additional fees or credit overpayment to our Deposit Account No. 04-0822.

Respectfully submitted,

DERGOSITS & NOAH LLP

Dated: April 17, 2002

By:

  
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PATENT



Sheet 1 of 1

FORM PTO-1449 (Rev. 7-80) Trademark Office	U.S. Dept. of Commerce Patent and Trademark Office	Atty. Docket No. 422.05	Appl. No. 10/050,654
LIST OF REFERENCES CITED BY APPLICANT (Use several sheets if necessary)		Applicant: CHEN, Ling, et al.	
		Filing Date: Jan 16, 2002	

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	4,058,430	15-Nov-1977	Method For Producing Compound Thin Films			25-Nov-1977
	4,389,973	28-Jun-1983	Apparatus For Performing Growth of Compound Thin Films			11-Dec-1981
	4,413,022	1-Nov-1983	Method For Performing Growth of Compound Thin Films			21-Jun-1979
	4,767,494	30-Aug-1988	Preparation process of compound semiconductor			19-Sep-1986
	4,806,321	21-Feb-1989	Use of infrared radiation and an ellipsoidal reflection mirror			25-Jul-1985
	4,840,921	20-Jun-1989	Process for the growth of III-V group compound semiconductor crystal on a Si substrate			30-Jun-1988
	4,845,049	4-Jul-1989	Doping III-V compound semiconductor devices with group VI monolayers using ALE			28-Mar-1988
	4,859,627	22-Aug-1989	Group VI doping of III-V semiconductors during ALE			1-Jul-1988
	4,861,417	29-Aug-1989	Method of growing group III-V compound semiconductor epitaxial layer			24-Mar-1988
	4,876,218	24-Oct-1989	Method of growing GaAs films on Si or GaAs substrates using ALE			26-Sep-1988
	4,993,357	19-Feb-1991	Apparatus for atomic layer epitaxial growth			21-Dec-1989
	5,082,798	21-Jan-1992	Crystal growth method			27-Sep-1990
	5,130,269	14-Jul-1992	Hetero-epitaxially grown compound semiconductor substrate and a method of growing the same			25-Apr-1989
	5,166,092	24-Nov-1992	Method of growing compound semiconductor epitaxial layer by atomic layer epitaxy			30-Oct-1990
	5,225,366	6-Jul-1993	Apparatus For and a Method of Growing Thin Films Elemental Semiconductors			22-Jun-1990
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	5,256,244	26-Oct-1993	Production of diffuse reflective coatings by atomic layer epitaxy			10-Feb-1992
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	5,290,748	1-Mar-1994	Polymerization catalyst for olefines			16-Jul-1992
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	5,300,186	5-Apr-1994	Hetero-epitaxially grown compound semiconductor substrate and a method of growing the same			7-Apr-1992
	5,316,793	31-May-1994	Directed Effusive Beam Atomic Layer Epitaxy System and Method			27-Jul-1992

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	5,330,610	19-Jul-1994	Method of Digital E-Beam by Externally Controlled Closed-Loop Feedback			28-May-1993
	5,336,324	9-Aug-1994	Apparatus for depositing a coating on a substrate			4-Dec-1991
	5,338,389	16-Aug-1994	Method of epitaxially growing compound crystal and doping method therein			21-Apr-1993
	5,374,570	20-Dec-1994	Method of manufacturing active matrix display device using insulation layer formed by the ale method			19-Aug-1995
	5,395,791	7-Mar-1995	Growth of II VI laser diodes with quantum wells by atomic layer epitaxy and migration enhanced epitaxy			20-Oct-1993
	5,438,952	8-Aug-1995	Method of growing a semiconductor layer			31-Jan-1994
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	5,458,084	17-Oct-1995	X-ray wave diffraction optics constructed by atomic layer epitaxy			9-Dec-1993
	5,480,818	2-Jan-1996	Method for forming a film and method for manufacturing a thin film transistor			9-Feb-1993
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	5,483,919	16-Jan-1996	Atomic layer epitaxy method and apparatus			17-Aug-1994
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	5,637,530	10-Jun-1997	II-VI compound semiconductor epitaxial layers having low defects, method for producing and devices utilizing same			10-Jun-1996
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	5,744,192	28-Apr-1998	Method of using water vapor to increase the conductivity of copper deposited with CU(HFAC) TMVS			8-Nov-1996
	5,851,849	22-Dec-1998	Process for Passivating Semiconductor Laser Structures with Severe Steps in Surface Topography			22-May-1997
	5,855,680	5-Jan-1999	Apparatus For Growing Thin Films			28-Nov-1995
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	6,015,590	18-Jan-2000	Method for growing thin films			28-Nov-1995
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	6,043,177	28-Mar-2000	Modification of zeolite or molecular sieve membranes using atomic layer controlled chemical vapor deposition		21-Jan-1997
	6,090,442	18-Jun-2000	Method of growing films on substrates at room temperatures using catalyzed binary reaction sequence chemistry		2-Oct-1997
	6,110,530	29-Aug-2000	CVD method of depositing copper films by using improved organocopper precursor blend		25-Jun-1999
	6,113,977	5-Sep-2000	Method of growing a ZnS:Mn phosphor layer for use in thin-film electroluminescent components		11-Sep-1997
	6,124,158	26-Sep-2000	Method of reducing carbon contamination of a thin dielectric film by using gaseous organic precursors, inert gas, and ozone to react with carbon contaminants		8-Jun-1999
	6,124,158	26-Sep-2000	Formation of thin dielectric film on semiconductor substrate, includes introducing gaseous organic precursor to form bonded reactant, introducing second gaseous reactant into the reaction chamber with the bonded reactant		8-Jun-1999
	6,130,147	10-Oct-2000	Methods for forming group III-V arsenide-nitride semiconductor materials		18-Mar-1997
	6,139,700	31-Oct-2000	Method of and apparatus for forming a metal interconnection in the contact hole of a semiconductor device		30-Sep-1998
	6,143,659	7-Nov-2000	Method for manufacturing aluminum metal interconnection layer by atomic layer deposition method		27-Aug-1998
	6,174,377	16-Jan-2001	Processing Chamber for Atomic Layer Deposition Processes		4-Jan-1999
	6,174,809	16-Jan-2001	Method for forming metal layer using atomic layer deposition		15-Dec-1998
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	6,305,314	23-Oct-2001	Apparatus and concept for		17-Dec-1999

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Examiner	Date Considered
* Examiner: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.	

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